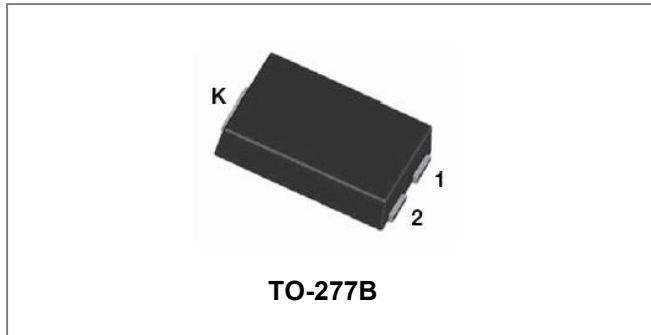


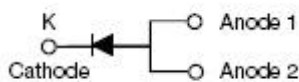
## MBR860S SCHOTTKY RECTIFIER



### Features

- Designed as Bypass Diodes for Solar Panels
- High Forward Surge Capability
- Ultra Low Forward Voltage Drop
- Excellent High Temperature Stability
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	-	60	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=80^\circ\text{C}$ , rectangular wave form	5	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3ms, Half Sine pulse, $T_c=25^\circ\text{C}$	150	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop *	$V_{F1}$	@ 5A, Pulse, $T_J = 25^\circ\text{C}$	0.63	0.65	V
	$V_{F2}$	@ 5A, Pulse, $T_J = 125^\circ\text{C}$	0.58	0.60	V
Reverse Current*	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	0.008	1.0	mA
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	3	20	mA
Junction Capacitance	$C_j$	@ $V_R = 5.0\text{ V}$ , $T_c=25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	260	400	pF

\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{\text{stg}}$	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Soldering Point	$R_{\theta\text{JS}}$	DC operation	1.5	$^{\circ}\text{C}/\text{W}$
Typical Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	DC operation	2.3	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	0.08	g

**Ratings and Characteristics Curves**

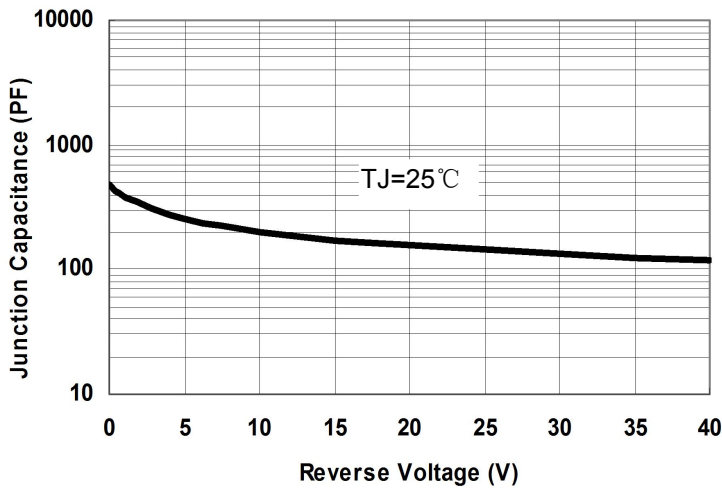


Fig.1-Typical Junction Capacitance

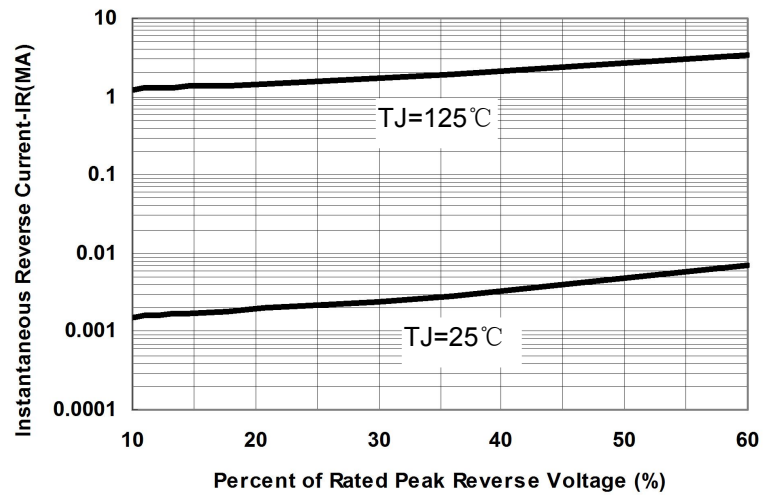


Fig.2-Typical Reverse Characteristics

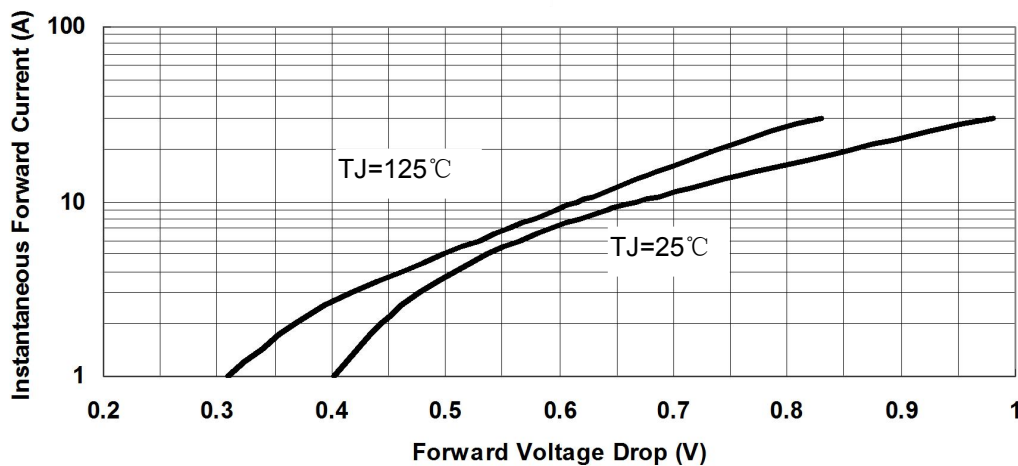
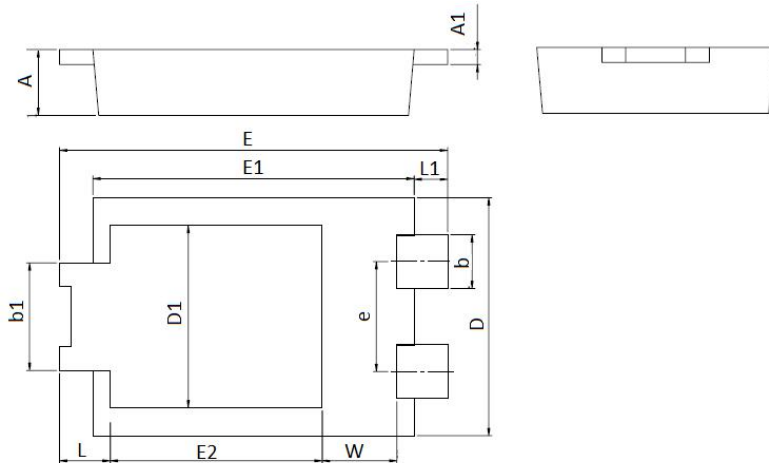


Fig.3-Typical Instantaneous Forward Voltage Characteristics

**Mechanical Dimensions TO-277B**


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.95	1.25	0.037	0.049
A1	0.20	0.30	0.008	0.012
b	0.85	0.95	0.033	0.037
b1	1.70	1.90	0.067	0.075
D	3.88	4.08	0.153	0.161
D1	2.90	3.20	0.114	0.126
e	1.74	1.94	0.069	0.076
E	6.30	6.70	0.248	0.264
E1	5.28	5.48	0.208	0.216
E2	3.40	3.70	0.134	0.146
L	0.70	1.00	0.028	0.039
L1	0.41	0.71	0.016	0.028
W	1.10	1.40	0.043	0.055

**Ordering Information**

Device	Package	Shipping
MBR860S	TO-277B(Pb-Free)	5000pcs/ reel

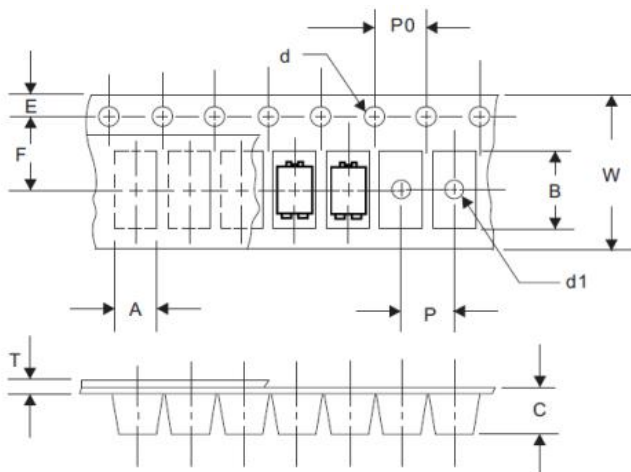
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Marking Diagram**


Where XXXXX is YYWWL

8 = Forward Current (8A)  
 60 = Reverse Voltage (60V)  
 S = Package type  
 YY = Year  
 WW = Week  
 L = Lot Number

**Cautions:** Molding resin  
 Epoxy resin UL:94V-0

**Carrier Tape Specification TO-277B**


SYMBOL	Millimeters	
	Min.	Max.
A	4.28	4.48
B	6.80	7.10
C	1.30	1.50
d	1.40	1.60
d1	-	1.50
E	1.65	1.85
F	5.40	5.60
P	7.90	8.10
P0	3.90	4.10
T	0.24	0.44
W	11.70	12.30

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